

# ITS42008-SB-D

Smart Octal High-Side NMOS-Power Switch

## Data Sheet

Rev 1.01, 2014-05-19

Standard Power



## 1 Overview

### Features

- Programmable Input thresholds: CMOS or  $V_S / 2$
- Switching all types of resistive, inductive and capacitive loads
- Fast demagnetization of inductive loads
- Very low standby current
- Optimized Electromagnetic Compatibility (EMC)
- Constant current source diagnostic output for overtemperature
- Overload protection
- Undervoltage shutdown with hysteresis
- Current limitation
- Short circuit protection
- Thermal shutdown with restart
- Overvoltage protection (including load dump)
- Reverse battery protection with external resistor
- Loss of GND and loss of Vbb protection
- Electrostatic Discharge Protection (ESD)
- Green Product (RoHS compliant)

ITS42008-SB-D is not qualified and manufactured according to the requirements of Infineon Technologies with regards to automotive and/or transportation applications.

### Description

The ITS42008-SB-D is a protected 200mΩ Smart Octal High-Side NMOS-Power Switch in a PG-DSO-36 power package with charge pump, CMOS or supply-ratiometric compatible input and constant current diagnostic feedback indicating overtemperature of the device.

### Product Summary

Overvoltage protection  $V_{SAZmin} = 47V$   
 Operating voltage range:  $11V < V_S < 45V$   
 On-state resistance  $R_{DSON} = \text{typ } 150m\Omega$   
 Operating Temperature range:  $T_j = -25^\circ C \text{ to } 125^\circ C$

### Application

- All types of resistive, inductive and capacitive loads.
- Driver for electromagnetic relays
- Power switch for 12V, 24V and 42V DC applications with CMOS compatible or high voltage control interface
- Micro controller or opto coupler compatible power switch with diagnosis feedback for overtemperature
- Power management for high-side-switching with low current consumption in OFF-mode



PG-DSO-36

Type	Package	Marking
ITS42008-SB-D	PG-DSO-36	I2008D

## 2 Block Diagram and Terms

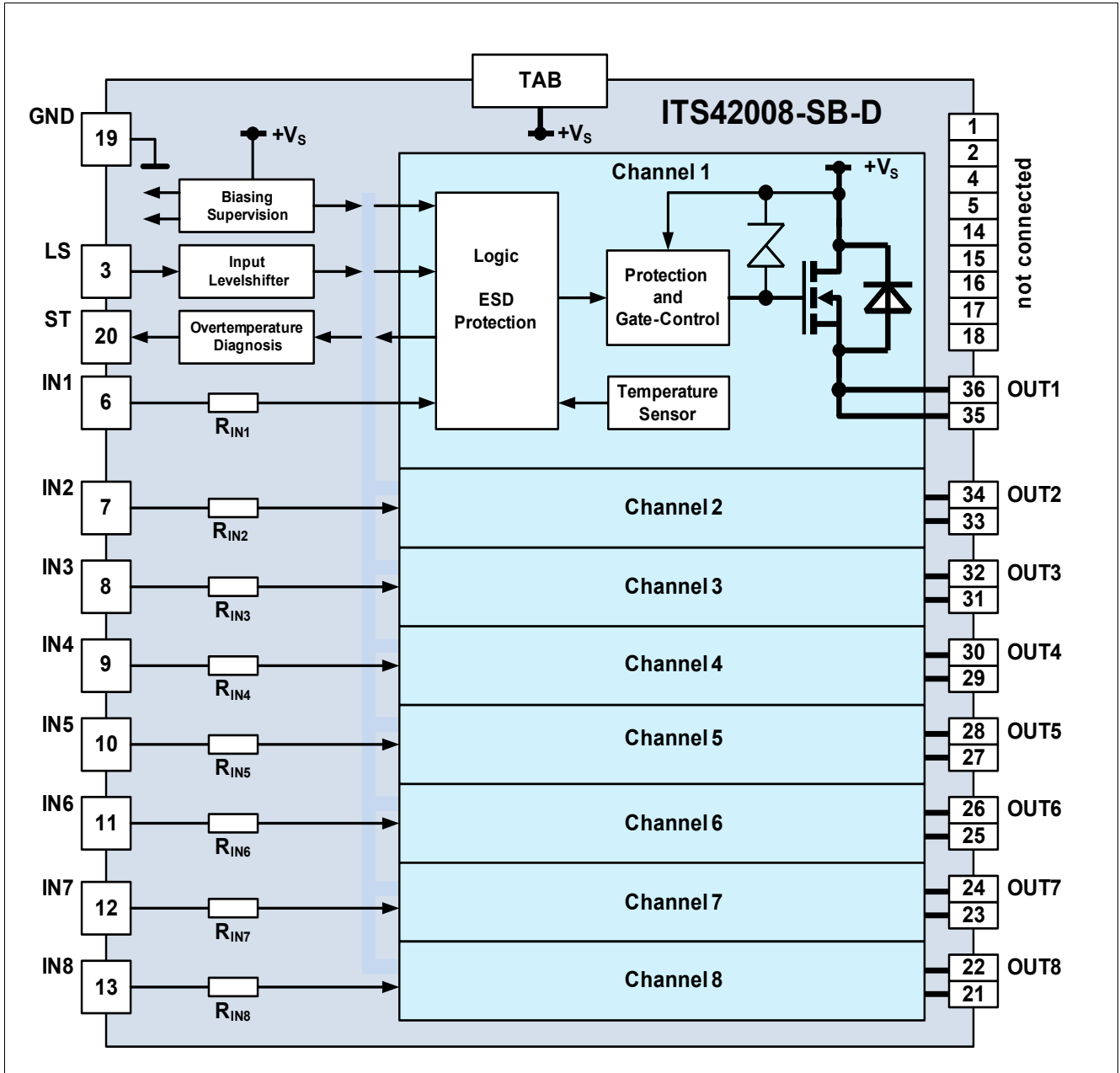
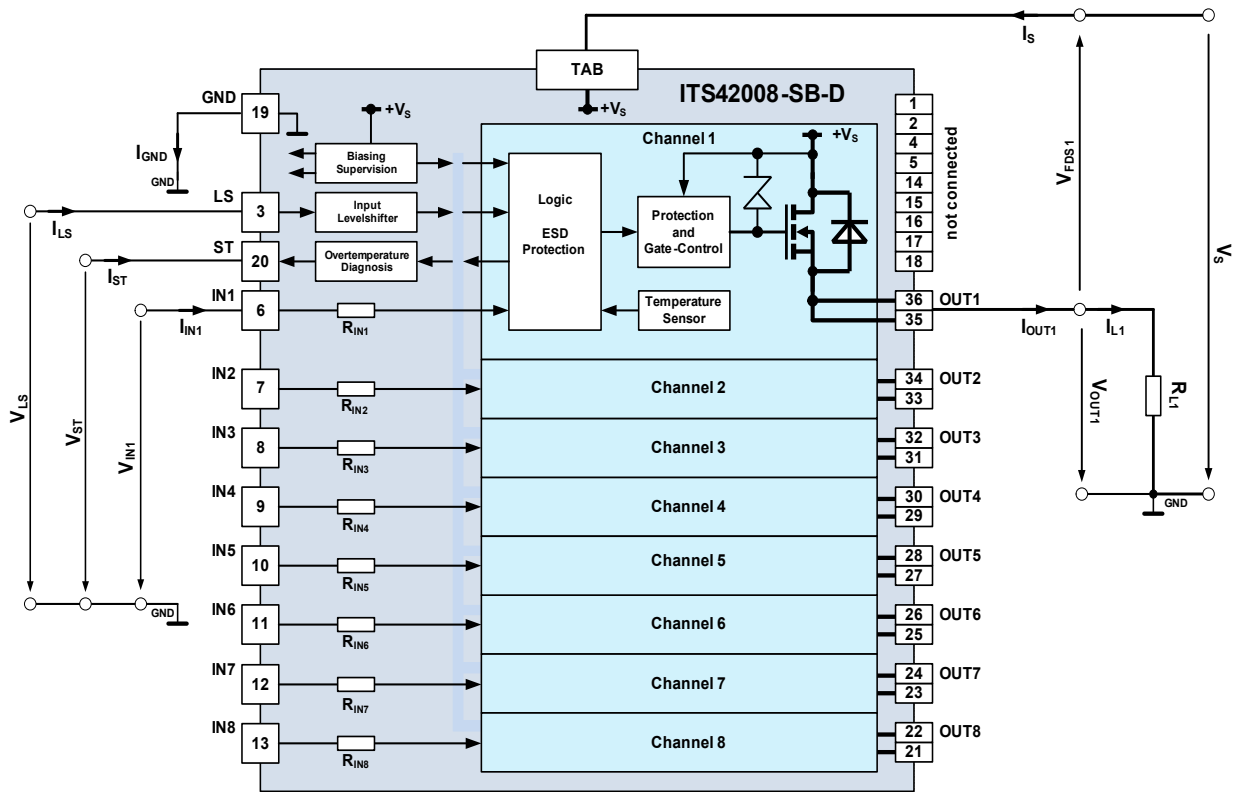


Figure 1 Block diagram

**Voltage- and Current-Definitions:**



**Switching Times and Slew Rate Definitions:**

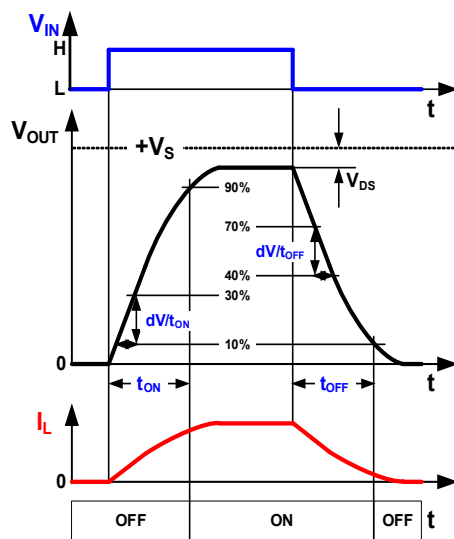


Figure 2 Terms - parameter definition

## 3 Pin Configuration

### 3.1 Pin Assignment

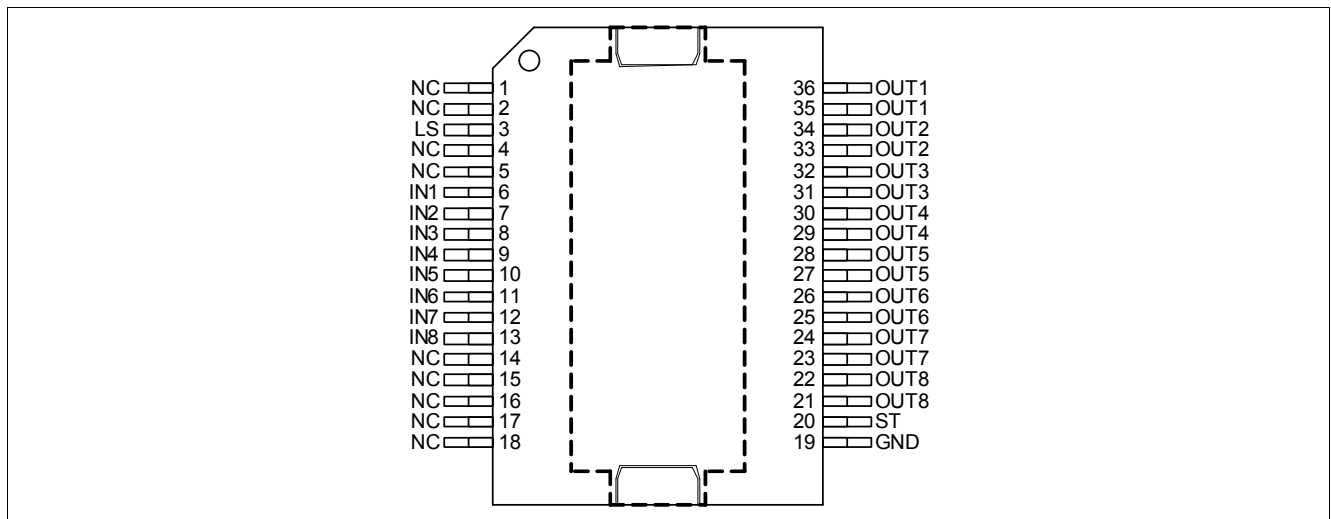


Figure 3 Pin configuration top view, PG-DSO-36

### 3.2 Pin Definitions and Functions

Pin	Symbol	Function
1, 2, 4, 5	NC	not connected
3	LS	Input level programming pin; Level: CMOS if LS=L; VS/2 if LS=H
6	IN1	Input channel 1, controls the power switch; the powerswitch is ON when IN1=H
7	IN2	Input channel 2, controls the power switch; the powerswitch is ON when IN2=H
8	IN3	Input channel 3, controls the power switch; the powerswitch is ON when IN3=H
9	IN4	Input channel 4, controls the power switch; the powerswitch is ON when IN4=H
10	IN5	Input channel 5, controls the power switch; the powerswitch is ON when IN5=H
11	IN6	Input channel 6, controls the power switch; the powerswitch is ON when IN6=H
12	IN7	Input channel 7, controls the power switch; the powerswitch is ON when IN7=H
13	IN8	Input channel 8, controls the power switch; the powerswitch is ON when IN8=H
14, 15, 16, 17, 18	NC	not connected
19	GND	Logic ground
20	ST	Status output (common diagnostic output); current source on in case of overtemperature; integrated pull down resistor to GND
21 and 22	OUT8	Output to the load of channel 8 (source of the DMOS power switch)
23 and 24	OUT7	Output to the load of channel 7 (source of the DMOS power switch)
25 and 26	OUT6	Output to the load of channel 6 (source of the DMOS power switch)
27 and 28	OUT5	Output to the load of channel 5 (source of the DMOS power switch)

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**Pin Configuration**

<b>Pin</b>	<b>Symbol</b>	<b>Function</b>
29 and 30	OUT4	Output to the load of channel 4 (source of the DMOS power switch)
31 and 32	OUT3	Output to the load of channel 3 (source of the DMOS power switch)
33 and 34	OUT2	Output to the load of channel 2 (source of the DMOS power switch)
35 and 36	OUT1	Output to the load of channel 1 (source of the DMOS power switch)
TAB	VS	Supply voltage (design the wiring for the maximum short circuit current and also for low thermal resistance)

## 4 General Product Characteristics

### 4.1 Absolute Maximum Ratings

**Table 1 Absolute maximum ratings <sup>1)</sup> at  $T_j = 25^\circ\text{C}$  unless otherwise specified. Currents flowing into the device unless otherwise specified in chapter "Block Diagram and Terms"**

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
<b>Supply voltage VS</b>							
Voltage	$V_S$			45	V		4.1.1
Voltage for short circuit protection	$V_{SSC}$			$V_S$	V		4.1.2
<b>Output stage OUTx</b>							
Output Current; (Short circuit current see electrical characteristics)	$I_{OUTx}$	- 2			A	self limited	4.1.3
<b>Reverse current through GND</b>							
Current	$I_{RGND}$			1.6	A	self limited	4.1.4
<b>Input INx (channel 1 to 8)</b>							
Voltage	$V_{INx}$	- 10		$V_S$	V		4.1.5
Current	$I_{IN}$	- 5		5	mA		4.1.6
<b>Input level programming LS</b>							
Voltage	$V_{LS}$	- 1		$V_S$	V		4.1.7
<b>Status ST</b>							
Voltage	$I_{LS}$	- 0.3			V	self limited	4.1.8
Current	$I_{LS}$			1	mA	self limited	4.1.9
<b>Temperatures</b>							
Junction Temperature	$T_j$	-40		125	$^\circ\text{C}$		4.1.10
Storage Temperature	$T_{stg}$	-55		125	$^\circ\text{C}$		4.1.11
<b>Power dissipation</b>							
$T_a = 25^\circ\text{C}^{2)}$	$P_{tot}$			3.3	W		4.1.12
<b>Inductive load switch-off energy dissipation</b>							
$T_j = 125^\circ\text{C}$ ; $IL = 625\text{mA}^{1)}$ ; all channels active	$E_{AS}$			1	J	single pulse	4.1.13
$T_j = 125^\circ\text{C}$ ; $IL = 625\text{mA}^{1)}$ ; one channel active	$E_{AS}$			10	J	single pulse	4.1.14
<b>ESD Susceptibility</b>							
ESD susceptibility (pins INx; LS and ST)	$V_{ESD}$	-1		1	kV	HBM <sup>3)</sup>	4.1.15
ESD susceptibility (all other pins)	$V_{ESD}$	-5		5	kV	HBM <sup>3)</sup>	4.1.16

1) Not subject to production test, specified by design

2) Device on 50mm\*50mm\*1.5mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70mm thick) copper area for V<sub>bb</sub> connection. PCB is vertical without blown air

3) ESD susceptibility HBM according to EIA/JESD 22-A 114.



## General Product Characteristics

Note: Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as “outside” the normal operating range. Protection functions are neither designed for continuous nor repetitive operation.

## 4.2 Functional Range

**Table 2 Functional Range**

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Nominal Operating Voltage	$V_S$	11		45	V	$V_S$ increasing	4.2.1

Note: Within the functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.

## 4.3 Thermal Resistance

Note: This thermal data was generated in accordance with JEDEC JESD51 standards. For more information, go to [www.jedec.org](http://www.jedec.org).

**Table 3 Thermal Resistance<sup>1)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Thermal Resistance - Junction to tab	$R_{thj-tab}$		2.8		K/W		4.3.1
Thermal Resistance - Junction to Ambient - 1s0p, minimal footprint	$R_{thJA\_1s0p}$		44.1		K/W	<sup>2)</sup>	4.3.2
Thermal Resistance - Junction to Ambient - 1s0p, 300mm <sup>2</sup>	$R_{thJA\_1s0p\_300mm^2}$		26.5		K/W	<sup>3)</sup>	4.3.3
Thermal Resistance - Junction to Ambient - 1s0p, 600mm <sup>2</sup>	$R_{thJA\_1s0p\_600mm^2}$		23.8		K/W	<sup>4)</sup>	4.3.4
Thermal Resistance - Junction to Ambient - 2s2p	$R_{thJA\_2s2p}$		19.9		K/W	<sup>5)</sup>	4.3.5
Thermal Resistance - Junction to Ambient with thermal vias - 2s2p	$R_{thJA\_2s2ptv}$		18.8		K/W	<sup>6)</sup>	4.3.6

1) Not subject to production test, specified by design

2) Specified  $R_{thJA}$  value is according to Jedec JESD51-3 at natural convection on FR4 1s0p board, footprint; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 1x 70μm Cu.

3) Specified  $R_{thJA}$  value is according to Jedec JESD51-3 at natural convection on FR4 1s0p board, Cu, 300mm<sup>2</sup>; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 1x 70μm Cu.

4) Specified  $R_{thJA}$  value is according to Jedec JESD51-3 at natural convection on FR4 1s0p board, 600mm<sup>2</sup>; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 1x 70μm Cu.

5) Specified  $R_{thJA}$  value is according to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70μm Cu, 2 x 35μm Cu).



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**General Product Characteristics**

- 6) Specified  $R_{thJA}$  value is according to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board with two thermal vias; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70 $\mu$ m Cu, 2 x 35 $\mu$ m Cu). The diameter of the two vias are equal 0.3mm and have a plating of 25 $\mu$ m with a copper heatsink area of 3mm x 2mm). JEDEC51-7: The two plated-through hole vias should have a solder land of no less than 1.25 mm diameter with a drill hole of no less than 0.85 mm diameter.

## 5 Electrical Characteristics

**Table 4**  $V_S = 15V$  to  $30V$ ;  $T_j = -25^\circ C$  to  $125^\circ C$ ;  $V_{LS} = 0V$ ; all voltages with respect to ground, currents flowing into the device unless otherwise specified in chapter "Block Diagram and Terms".  
Typical values at  $V_S = 13.5V$ ,  $T_j = 25^\circ C$ ; index "x" means "number of channel 1 to 8".

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
<b>Powerstages</b>							
NMOS ON Resistance	$R_{DSONx}$		150	200	m $\Omega$	$I_{OUTx} = 0.5A$ ; $T_j = 25^\circ C$ ; $V_{LS} = V_{INx} = V_S = 15V$	5.0.1
NMOS ON Resistance	$R_{DSONx}$		270	320	m $\Omega$	$I_{OUTx} = 0.5A$ ; $T_j = 125^\circ C$ ; $V_{LS} = V_{INx} = V_S = 15V$	5.0.2
<b>Timings of Power Stages<sup>1)</sup></b>							
Turn ON Time(to 90% of $V_{outx}$ ); L to H transition of $V_{INx}$	$t_{ONx}$		50	100	$\mu s$	$V_S = 15V$ ; $R_{Lx} = 47\Omega$	5.0.3
Turn OFF Time (to 10% of $V_{outx}$ ); H to L transition of $V_{INx}$	$t_{OFFx}$		75	150	$\mu s$	$V_S = 15V$ ; $R_{Lx} = 47\Omega$	5.0.4
ON-Slew Rate (10 to 30% of $V_{outx}$ ); L to H transition of $V_{INx}$	$SR_{ONx}$		1.0	2.0	V / $\mu s$	$V_S = 15V$ ; $R_{Lx} = 47\Omega$	5.0.5
OFF-Slew Rate (70 to 40% of $V_{outx}$ ); H to L transition of $V_{INx}$	$SR_{OFFx}$		1.0	2.0	V / $\mu s$	$V_S = 15V$ ; $R_{Lx} = 47\Omega$	5.0.6
<b>Under voltage lockout (charge pump start-stop-restart)</b>							
Supply undervoltage; charge pump stop voltage	$V_{SUV}$	7.0		10.5	V	$V_S$ decreasing	5.0.7
Supply startup voltage; Charge pump restart voltage	$V_{SSU}$			11.0	V	$V_S$ increasing	5.0.8
Supply undervoltage hysteresis	$V_{SUHY}$		0.5		V	$V_{SUHY} = V_{SSU} - V_{SUV}$	5.0.9
<b>Current consumption</b>							
Operating current	$I_{GND}$		5	12	mA	$V_{INx} = V_{LS} = V_S = 30V$	5.0.10
Standby current	$I_{SSTB}$		50	150	$\mu A$	$V_{INx} = 6.5V$ ; $V_{LS} = V_S = 15V$ ; $V_{OUTx} = 0V$	5.0.11
Output leakage current	$I_{OUTLKx}$		5	10	$\mu A$	$V_{INx} = 6.5V$ ; $V_{LS} = V_S = 15V$ $V_{OUTx} = 0V$	5.0.12
<b>Protection functions<sup>2)</sup></b>							
Initial peak short circuit current limit	$I_{LSCPx}$			1.9	A	$T_j = -25^\circ C$ $V_{LS} = V_S = V_{INx} = 30V$ ; $t_{mx} = 700\mu s$	5.0.13

## Electrical Characteristics

**Table 4**  $V_S = 15V$  to  $30V$ ;  $T_j = -25^\circ C$  to  $125^\circ C$ ;  $V_{LS} = 0V$ ; all voltages with respect to ground, currents flowing into the device unless otherwise specified in chapter “Block Diagram and Terms”.  
Typical values at  $V_S = 13.5V$ ,  $T_j = 25^\circ C$ ; index “x” means “number of channel 1 to 8”.

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Initial peak short circuit current limit	$I_{LSCPx}$		1.4		A	$T_j = 25^\circ C$ $V_{LS} = V_S = V_{INx} = 30V$ ; $t_{mx} = 700\mu s$	5.0.14
Initial peak short circuit current limit	$I_{LSCPx}$	0.7			A	$T_j = 125^\circ C$ $V_{LS} = V_S = V_{INx} = 30V$ ; $t_{mx} = 700\mu s$	5.0.15
Repetitive short circuit current limit $T_j = T_{jTrip}$ ; see timing diagrams	$I_{LSCRx}$		1.1		A	$V_{INx} = 5.0V$ ;	5.0.16
Output clamp at $V_{OUTx} = V_S - V_{DSCLx}$ (inductive load switch off)	$V_{DSCLx}$	47	53	60	V	$I_{OUTx} = 4mA$ ; $V_{LS} = 30V$	5.0.17
Oversvoltage protection	$V_{SAZ}$	47			V	$I_S = 4mA$ $V_{LS} = 30V$	5.0.18
Thermal overload trip temperature	$T_{jTrip}$	135			$^\circ C$		5.0.19
Thermal hysteresis	$T_{HYS}$		10		K		5.0.20
<b>Reverse Battery<sup>3)</sup></b>							
Continuous reverse battery voltage	$V_{SREV}$			45	V		5.0.21
Forward voltage of the drain-source reverse diode	$V_{FDSx}$			1.2	V	$I_{FDS} = 1.25A$ ; $V_{IN} = 0V$	5.0.22
<b>Input interface; pin INx</b>							
Input turn-ON threshold voltage	$V_{INONx}$	2.2			V	LS = L; CMOS mode	5.0.23
Input turn-OFF threshold voltage	$V_{INOFFx}$			0.8	V	LS = L; CMOS mode	5.0.24
Input turn-ON threshold voltage	$V_{INONx}$	$V_{ST} / 2 + 1$			V	LS = H or open; ratiometric mode	5.0.25
Input turn-OFF threshold voltage	$V_{INOFFx}$			$V_{ST} / 2 - 1$	V	LS = H or open; ratiometric mode	5.0.26
Input threshold hysteresis	$V_{INHYSx}$		0.3		V		5.0.27
Off state input current	$I_{INOFFx}$	8			$\mu A$	LS = L; CMOS mode $V_{INx} = 0.8V$	5.0.28
On state input current	$I_{INONx}$			70	$\mu A$	LS = L; CMOS mode $V_{INx} = 2.2V$	5.0.29
Off state input current	$I_{INOFFx}$	80			$\mu A$	LS = H or open; ratiometric mode $V_{INx} = V_{ST} / 2 - 1$	5.0.30
On state input current	$I_{INONx}$			260	$\mu A$	LS = H or open; ratiometric mode $V_{INx} = V_{ST} / 2 + 1$	5.0.31
Input switch ON delay time	$t_{dON}$	150	340		$\mu s$		5.0.32

## Electrical Characteristics

**Table 4**  $V_S = 15V$  to  $30V$ ;  $T_j = -25^{\circ}C$  to  $125^{\circ}C$ ;  $V_{LS} = 0V$ ; all voltages with respect to ground, currents flowing into the device unless otherwise specified in chapter “Block Diagram and Terms”. Typical values at  $V_S = 13.5V$ ,  $T_j = 25^{\circ}C$ ; index “x” means “number of channel 1 to 8”.

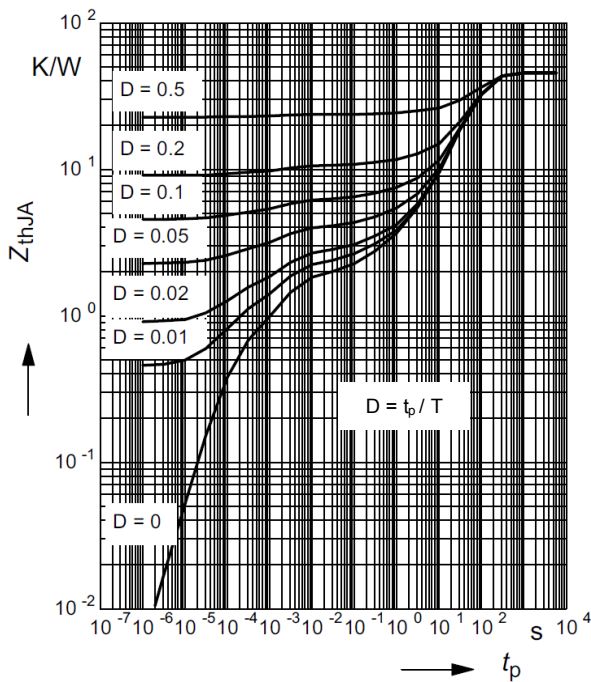
Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Input resistance	$R_{INx}$	2	3	5	k $\Omega$		5.0.33
<b>Input interface; pin LS</b>							
Pull down resistance	$R_{LS}$	300	800		k $\Omega$	$V_{LS} = V_S = 15V$	5.0.34
<b>Status output (current source); pin ST</b>							
Status output current	$I_{ST}$	2	3	4	mA	$V_{ST} = 5V$ $V_{LS} = V_S = 30V$	5.0.35
Status leakage current	$I_{STLK}$	- 2			$\mu A$	$V_{ST} = 0V$ ; $T_j < 135^{\circ}C$ ; $V_{LS} = V_S = 30V$	5.0.36

- 1) Timing values only with high slewrate input signal; otherwise slower.
- 2) Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as “outside” normal operating range. Protection functions are not designed for continuous repetitive operation.
- 3) Requires a 150W resistor in GND connection. The reverse load current trough the intrinsic drain-source diode of the power-M

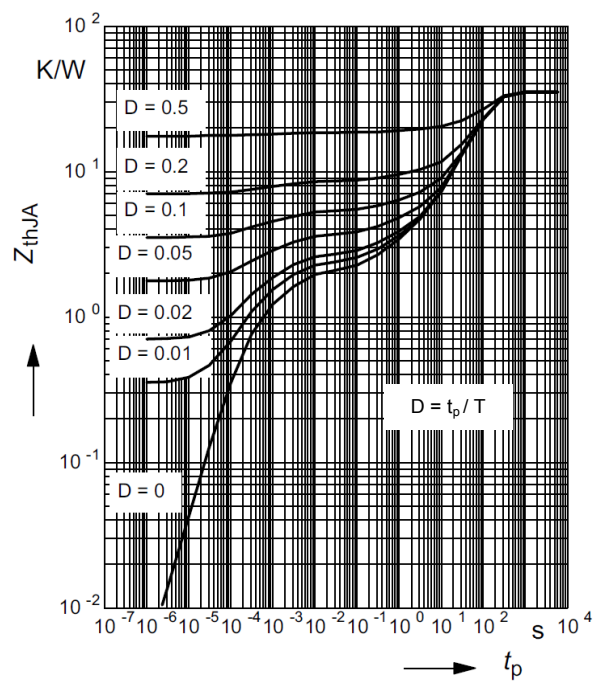
## 6 Typical Performance Graphs

### Typical Characteristics

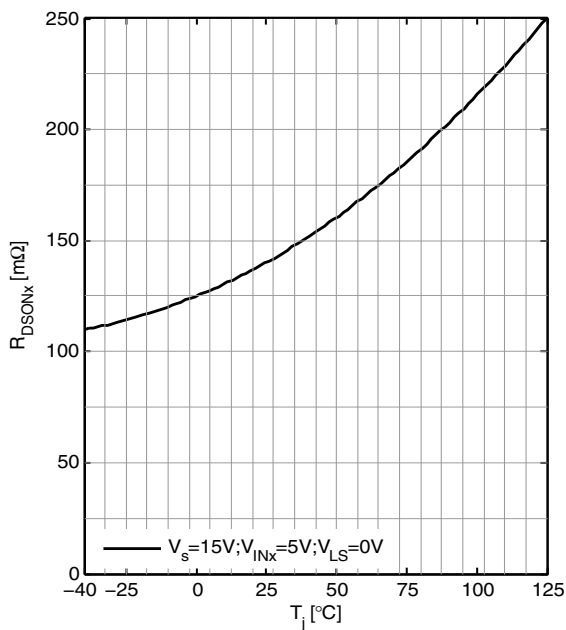
Transient Thermal Impedance  $Z_{thJA}$  versus Pulse Time  $t_p$  @ 6cm<sup>2</sup> heatsink area



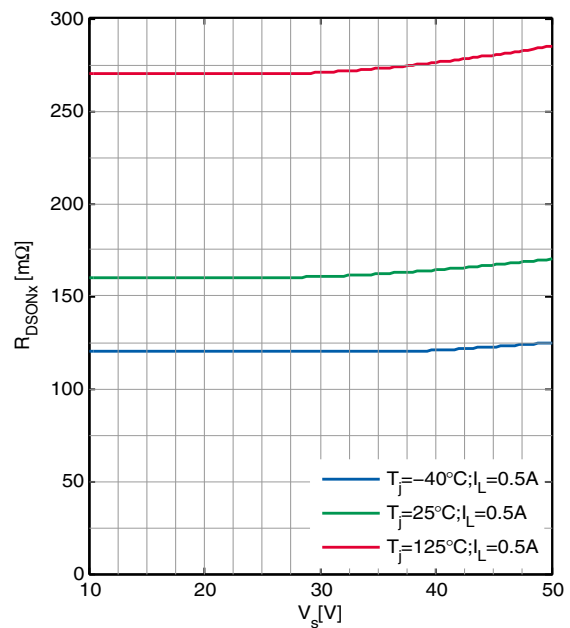
Transient Thermal Impedance  $Z_{thJA}$  versus Pulse Time  $t_p$  @ min footprint



On-Resistance  $R_{DS(on)}$  versus Junction Temperature  $T_j$

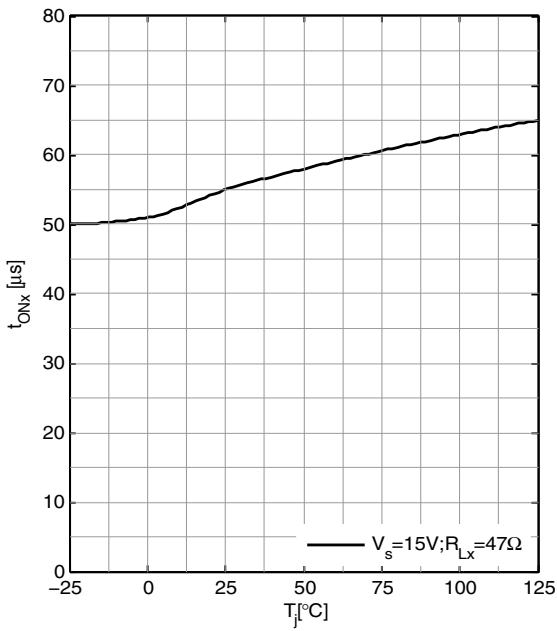


On-Resistance  $R_{DS(on)}$  versus Supply Voltage  $V_s$

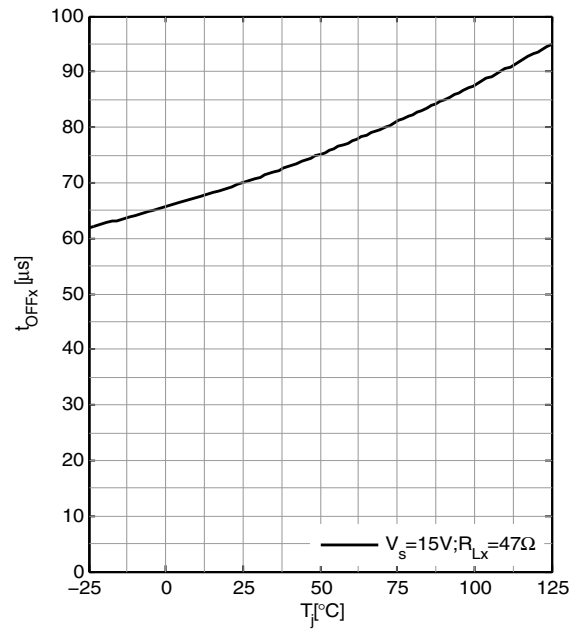


Typical Characteristics

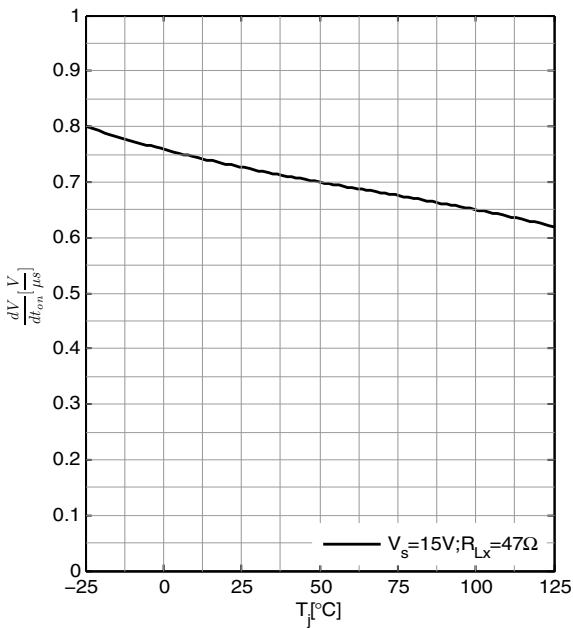
Switch ON Time  $t_{ONx}$  versus Junction Temperature  $T_j$



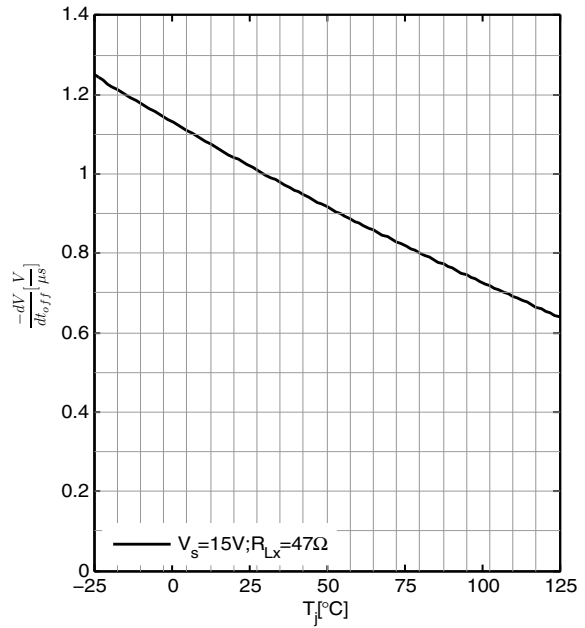
Switch OFF Time  $t_{OFFx}$  versus Junction Temperature  $T_j$



ON Slewrate  $SR_{ONx}$  versus Junction Temperature  $T_j$

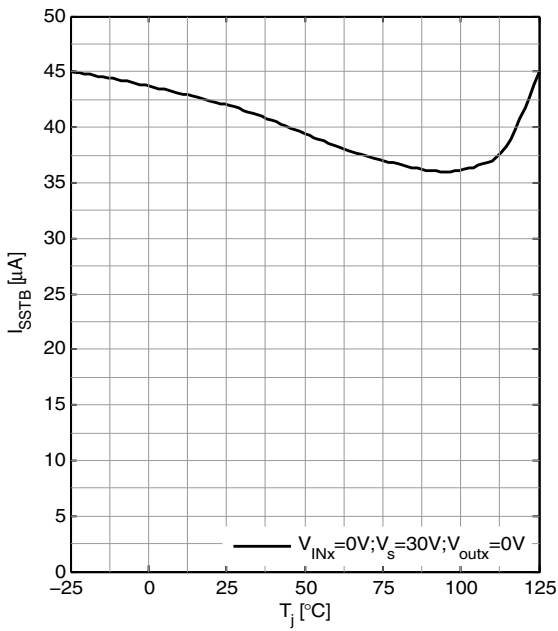


OFF Slewrate  $SR_{OFFx}$  versus Junction Temperature  $T_j$

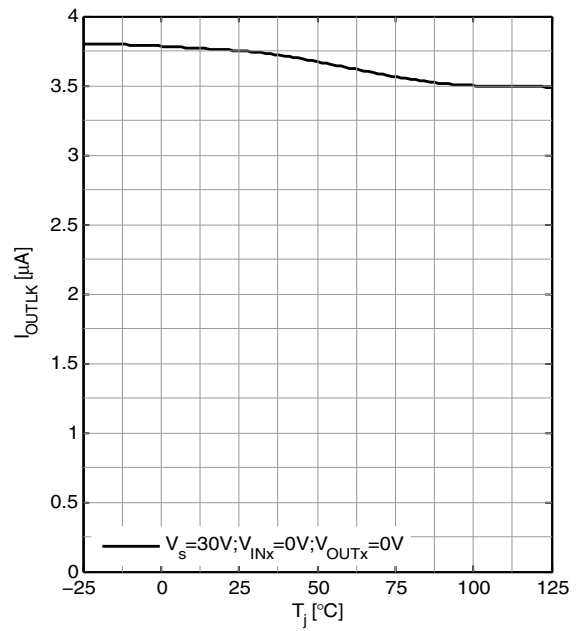


Typical Characteristics

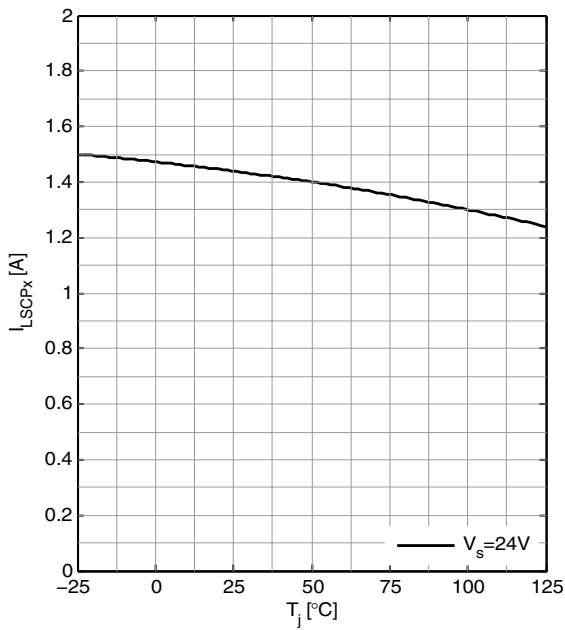
Standby Current  $I_{SSTB}$  versus Junction Temperature  $T_j$



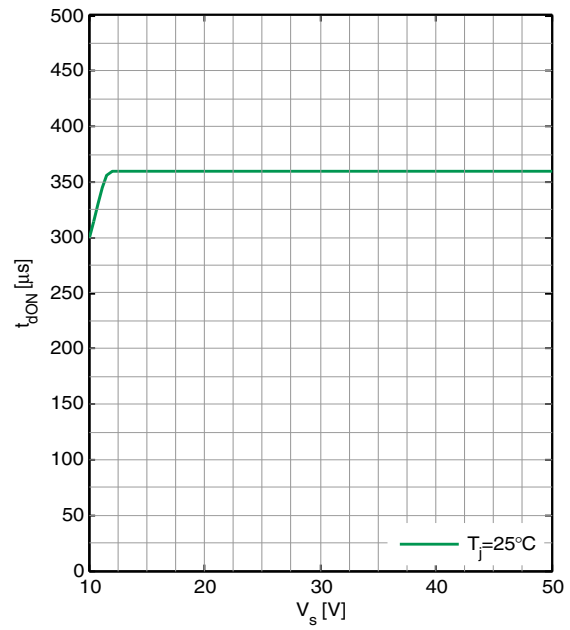
Output Leakage current  $I_{OUTLKx}$  versus Junction Temperature  $T_j$



Initial Peak Short Circuit Current Limit  $I_{LSCPx}$  versus Junction Temperature  $T_j$



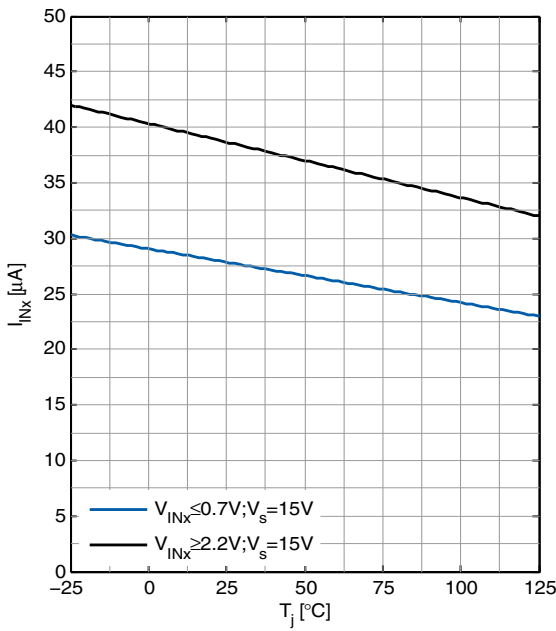
Initial Short Circuit Shutdown time  $t_{dON}$  versus Junction Temperature  $T_j$



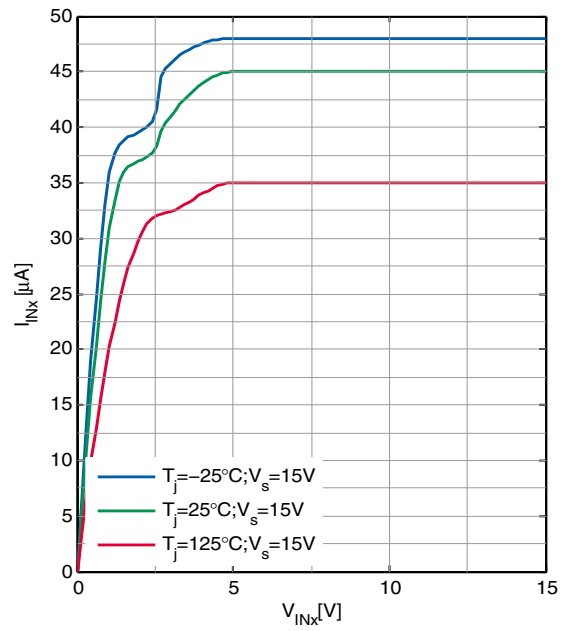


Typical Characteristics

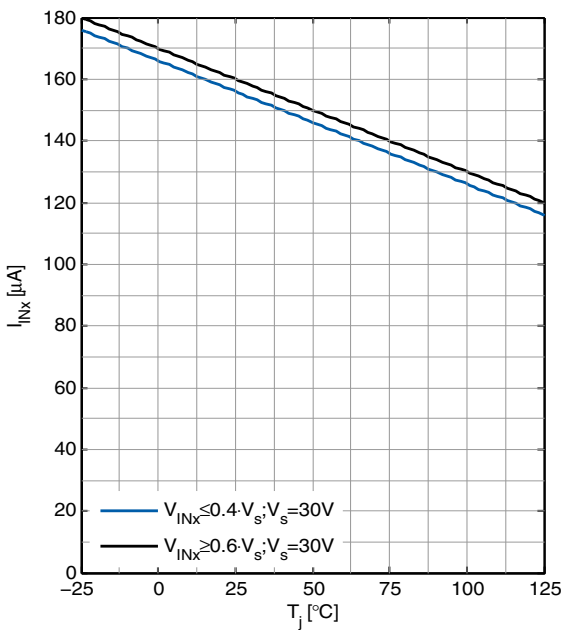
Input Current Consumption  $I_{INx}$  versus Junction Temperature  $T_j$



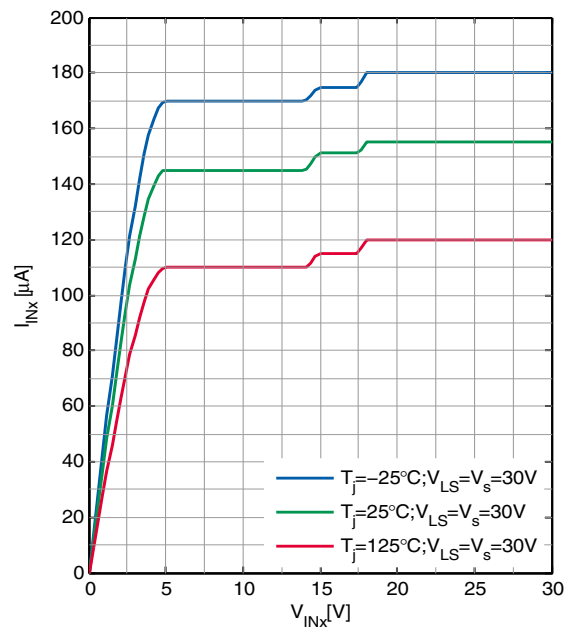
Input Current Consumption  $I_{INx}$  versus Input voltage  $V_{IN}$



Input Current Consumption  $I_{INx}$  versus Junction Temperature  $T_j$

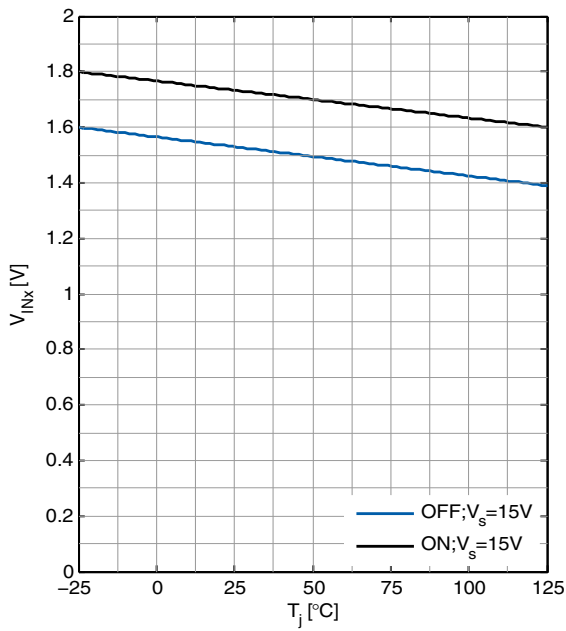


Input Current Consumption  $I_{INx}$  versus Input voltage  $V_{IN}$

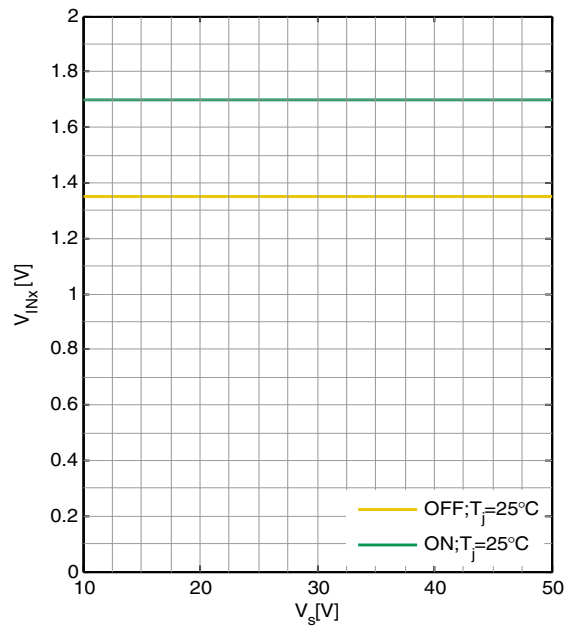


Typical Characteristics

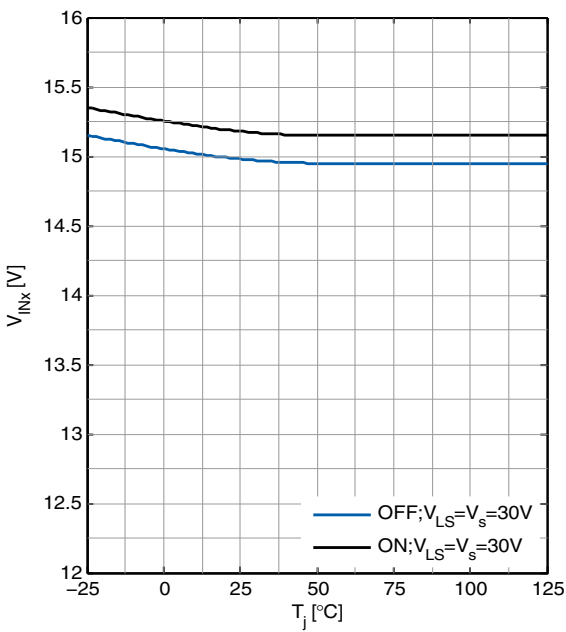
Input Threshold voltage  $V_{INH,Lx}$  versus Junction Temperature  $T_j$



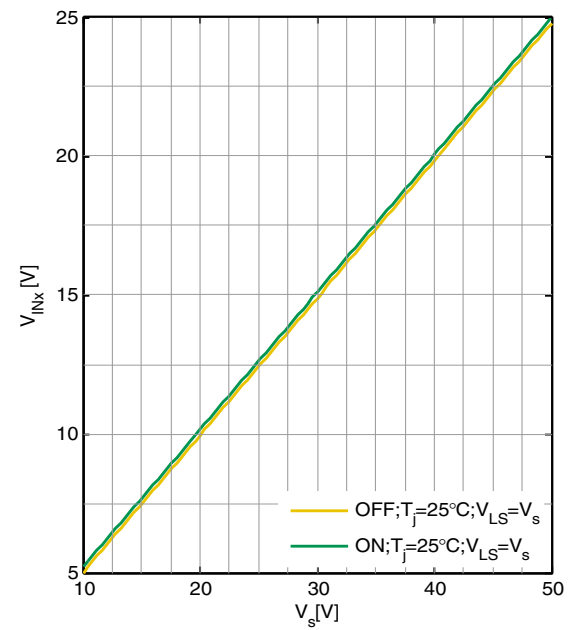
Input Threshold voltage  $V_{INH,Lx}$  versus Supply Voltage  $V_s$



Input Threshold voltage  $V_{INH,Lx}$  versus Junction Temperature  $T_j$

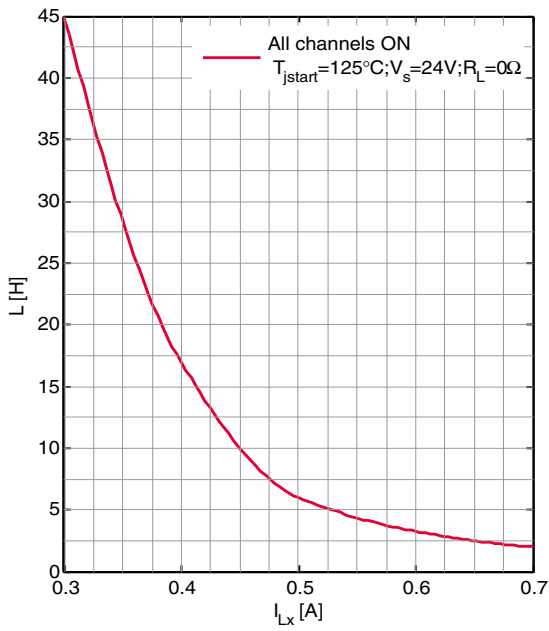


Input Threshold voltage  $V_{INH,Lx}$  versus Supply Voltage  $V_s$

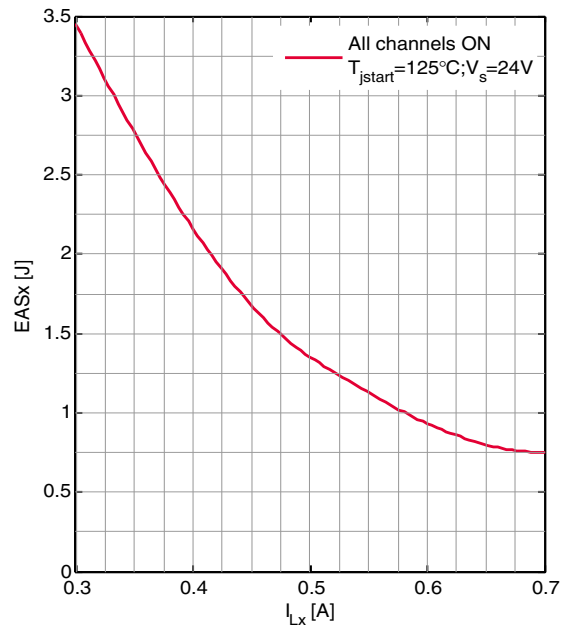


Typical Characteristics

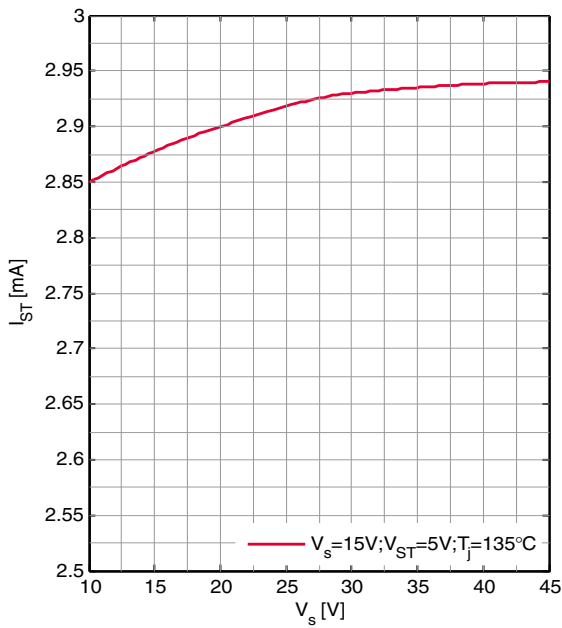
Max. allowable Load Inductance  $L$  versus Load current  $I_{Lx}$



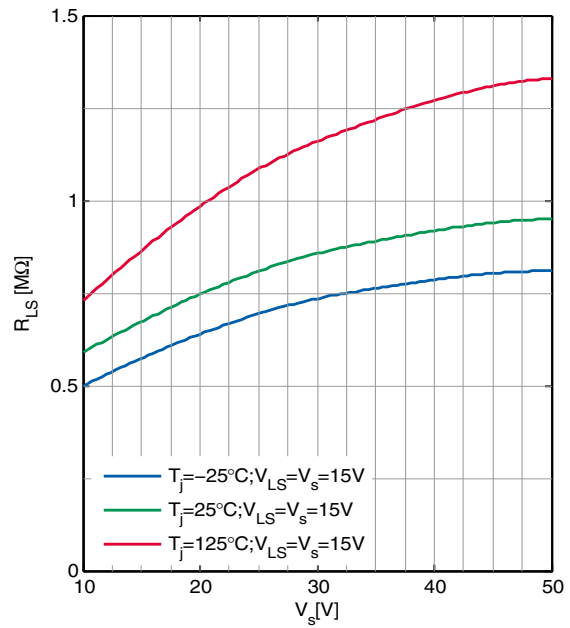
Max. allowable Inductive single pulse Switch-off Energy  $E_{AS}$  versus Load current  $I_{Lx}$



Status Output Current  $I_{ST}$  versus Supply Voltage  $V_s$



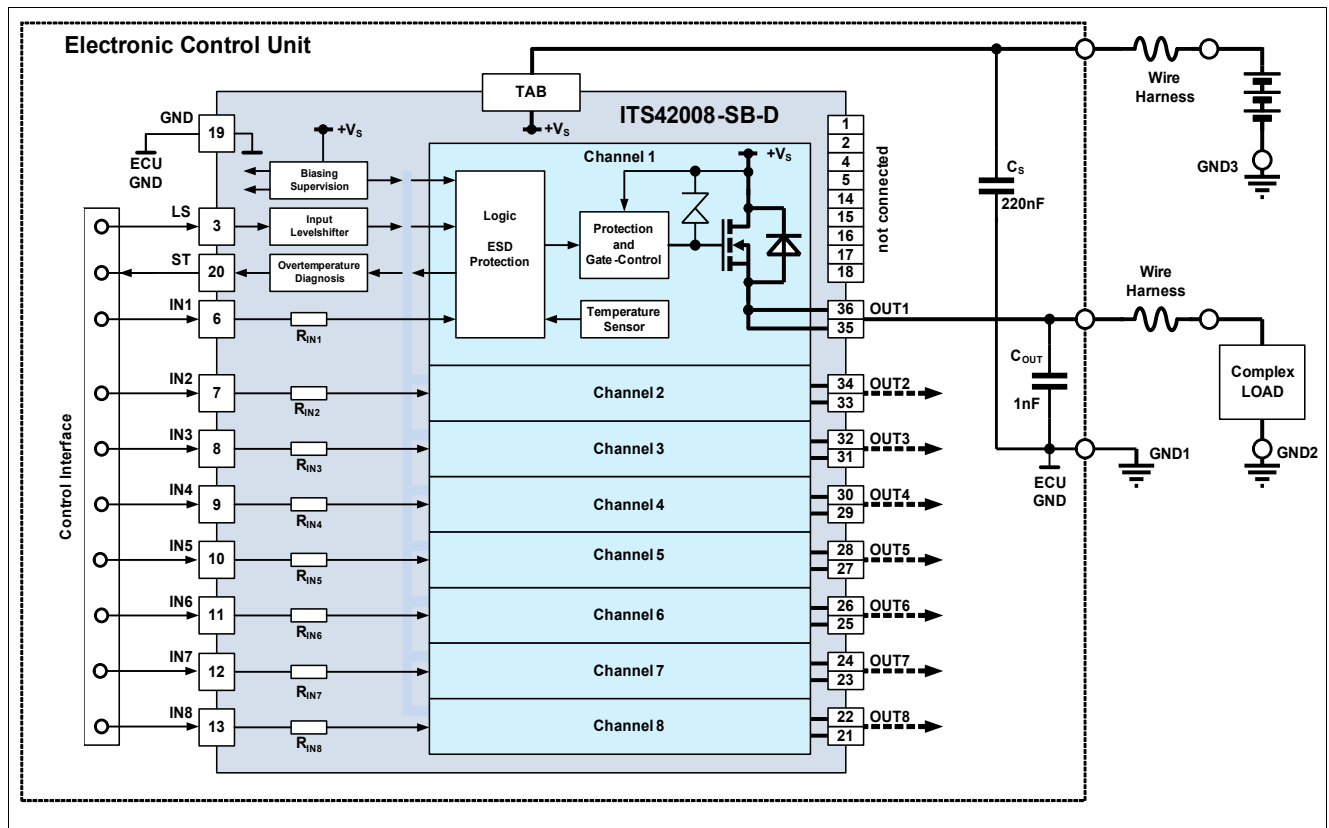
Internal pull down Resistor  $R_{LS}$  at pin LS versus Supply Voltage  $V_s$



## 7 Application Information

### 7.1 Application Diagram

The following information is given as a hint for the implementation of the device only and shall not be regarded as a description or warranty for a certain functionality, condition or quality of the device.



**Figure 4 Application Diagram**

The ITS42008-SB-D can be connected directly to the battery of a supply network. It is recommended to place a ceramic capacitor (e.g.  $C_S = 220\text{nF}$ ) between supply and GND of the ECU to avoid line disturbances. Wire harness inductors/resistors are sketched in the application circuit above.

The complex load (resistive, capacitive or inductive) must be connected to the output pin OUT.

A built-in current limit protects the device against destruction.

The ITS42008-SB-D can be switched on and off with ground related standard logic signal at pin  $IN_x$  if the level programming pin LS is set to L.

If LS is connected to the supply voltage  $V_S$  the input threshold is set to  $\sim 50\%$  of  $V_S$ .

To achieve a higher robustness it is recommended to connect the LS pin to GND or Supply voltage.

If the pin LS is left open the thresholds are automatically set to CMOS level caused by an internal high ohmic pull down resistor to GND.

In standby mode (all inputs  $IN_x=L$ ) the ITS42008-SB-D is deactivated with very low current consumption.

The output voltage slope is controlled during on and off transition to minimize emissions. Only a small ceramic capacitor  $C_{OUT}=1\text{nF}$  is recommended to attenuate RF noise.

In the following chapters the main features, some typical waveforms and the protection behaviour of the ITS42008-SB-D is shown. For further details please refer to application notes on the Infineon homepage.

## 7.2 Diagnosis Description

For diagnostic purpose the device provides a digital output pin ST in order to indicate fault conditions.

The status output (ST) of the ITS42008-SB-D is a high voltage current source.

In “normal” operation mode (no overtemperature) the current source is switched OFF. An internal pull down resistor pulls pin ST down to GND. In case of overtemperature the current source is activated. To limit the voltage at pin ST an external zenerdiode to GND must be added.

The following truth table defines the status output.

**Table 5 Truth Table of diagnosis feature**

Device Operation	INx	OUTx	current source at ST	Comment
Normal Operation	L	L	OFF	
Normal Operation	H	H	OFF	
Short circuit to GND	L	L	OFF	
Short circuit to GND	H	L	OFF	
Undervoltage at $V_S$	L	L	OFF	
Undervoltage at $V_S$	H	L	OFF	
Overtemperature	L	L	OFF	
Overtemperature	H	L	ON	toggeling with restart

### 7.3 Special Feature Description

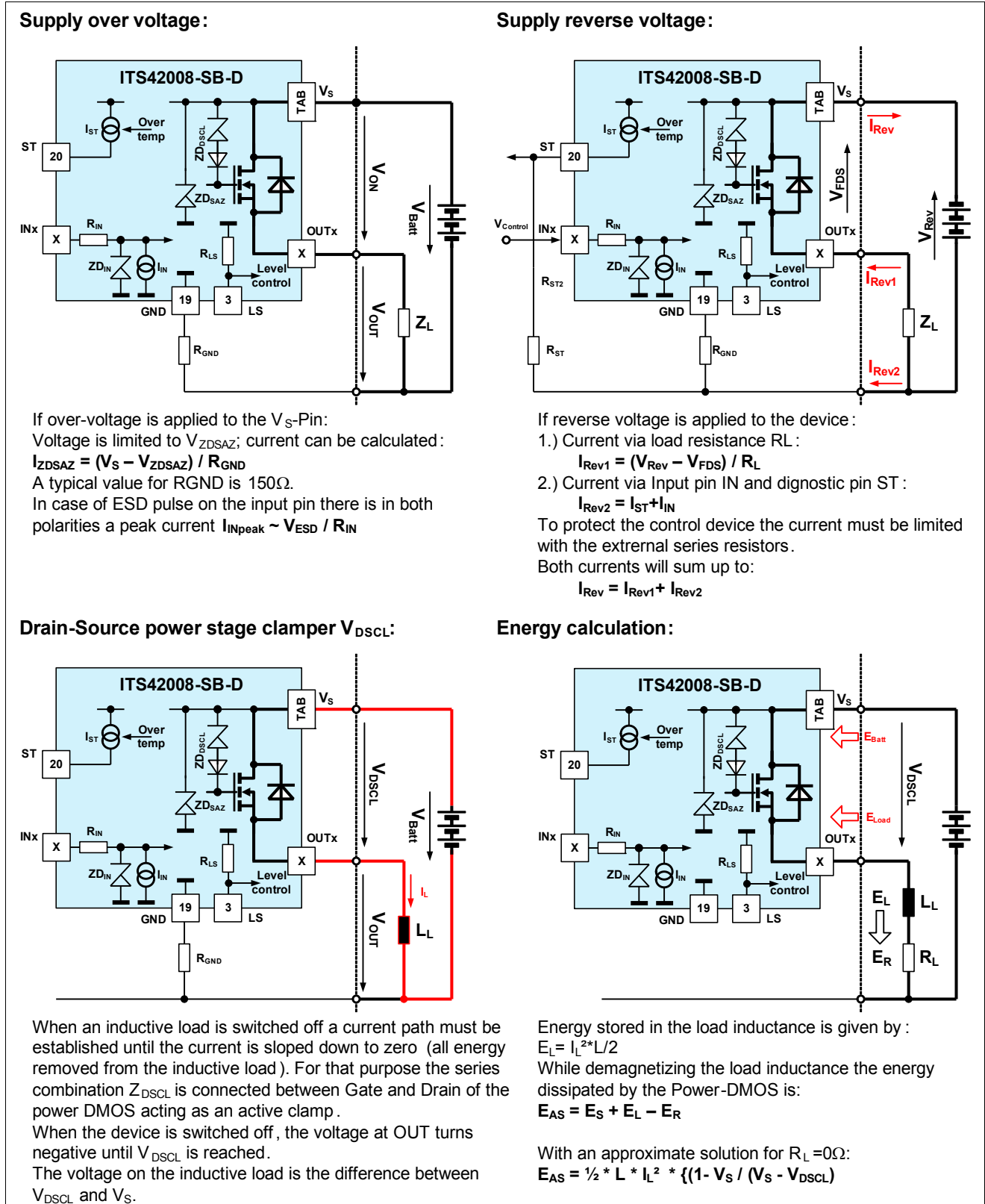


Figure 5 Special feature description

## 7.4 Typical Application Waveforms

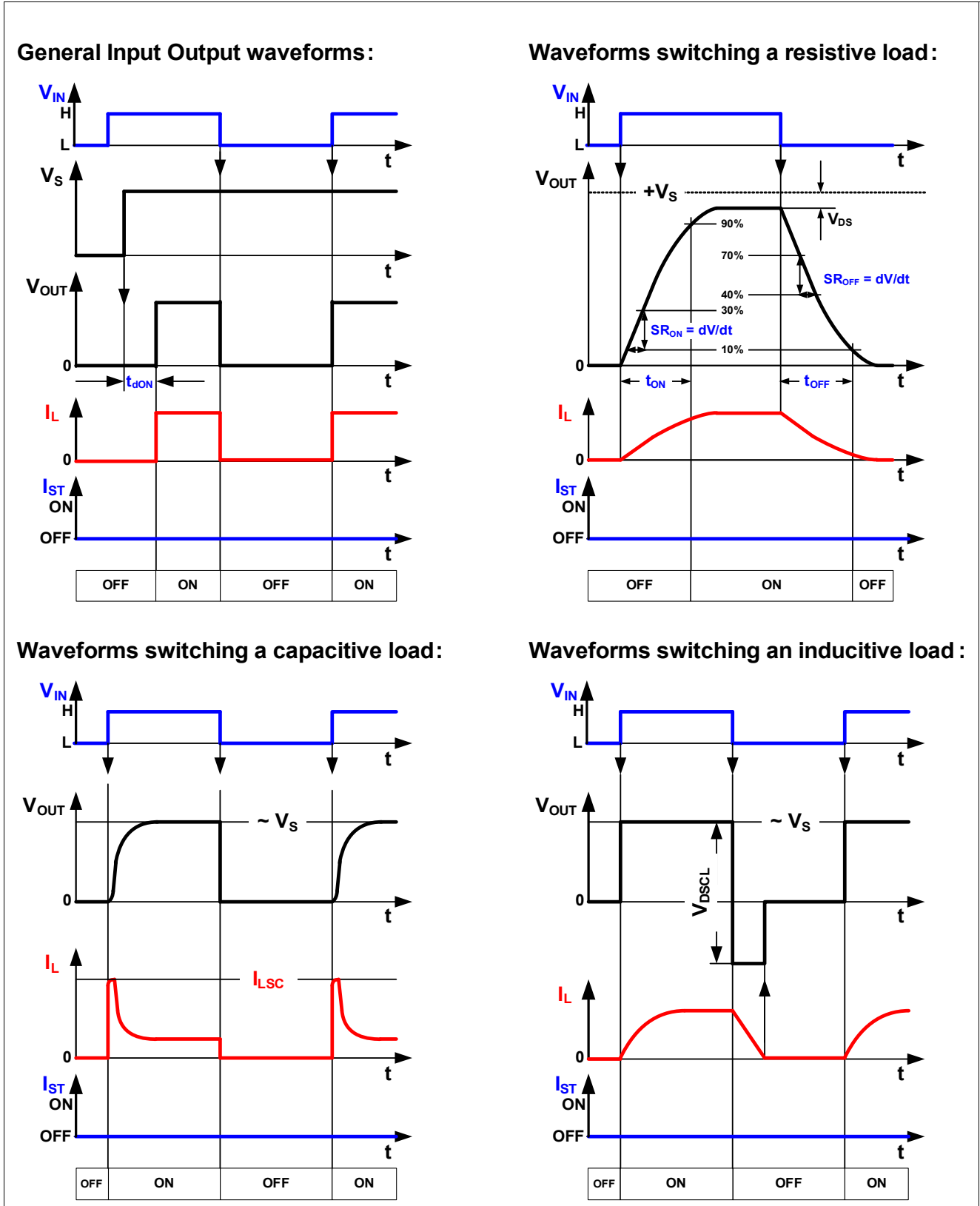


Figure 6 Typical application waveforms of the ITS42008-SB-D



## 7.5 Protection Behavior

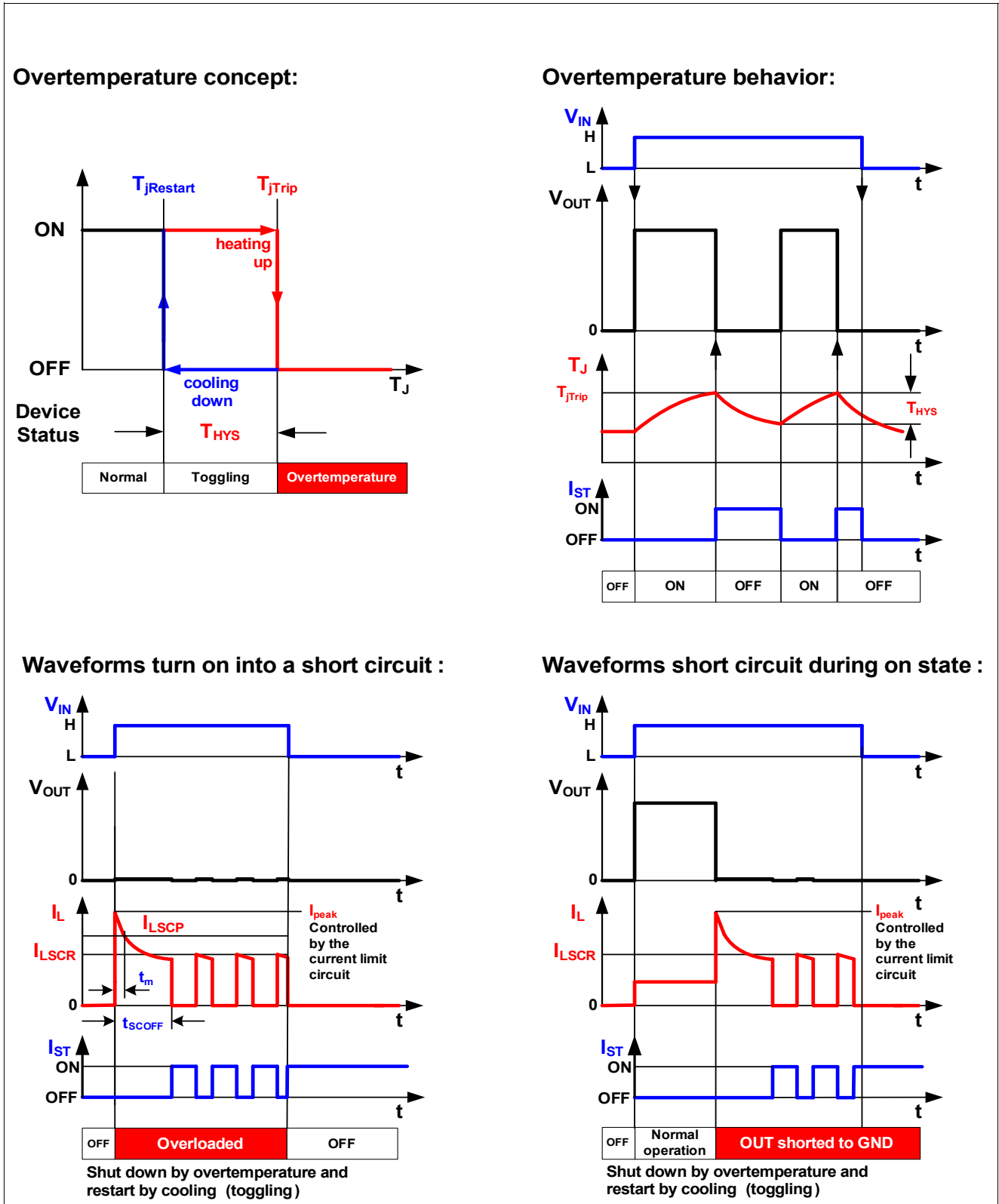
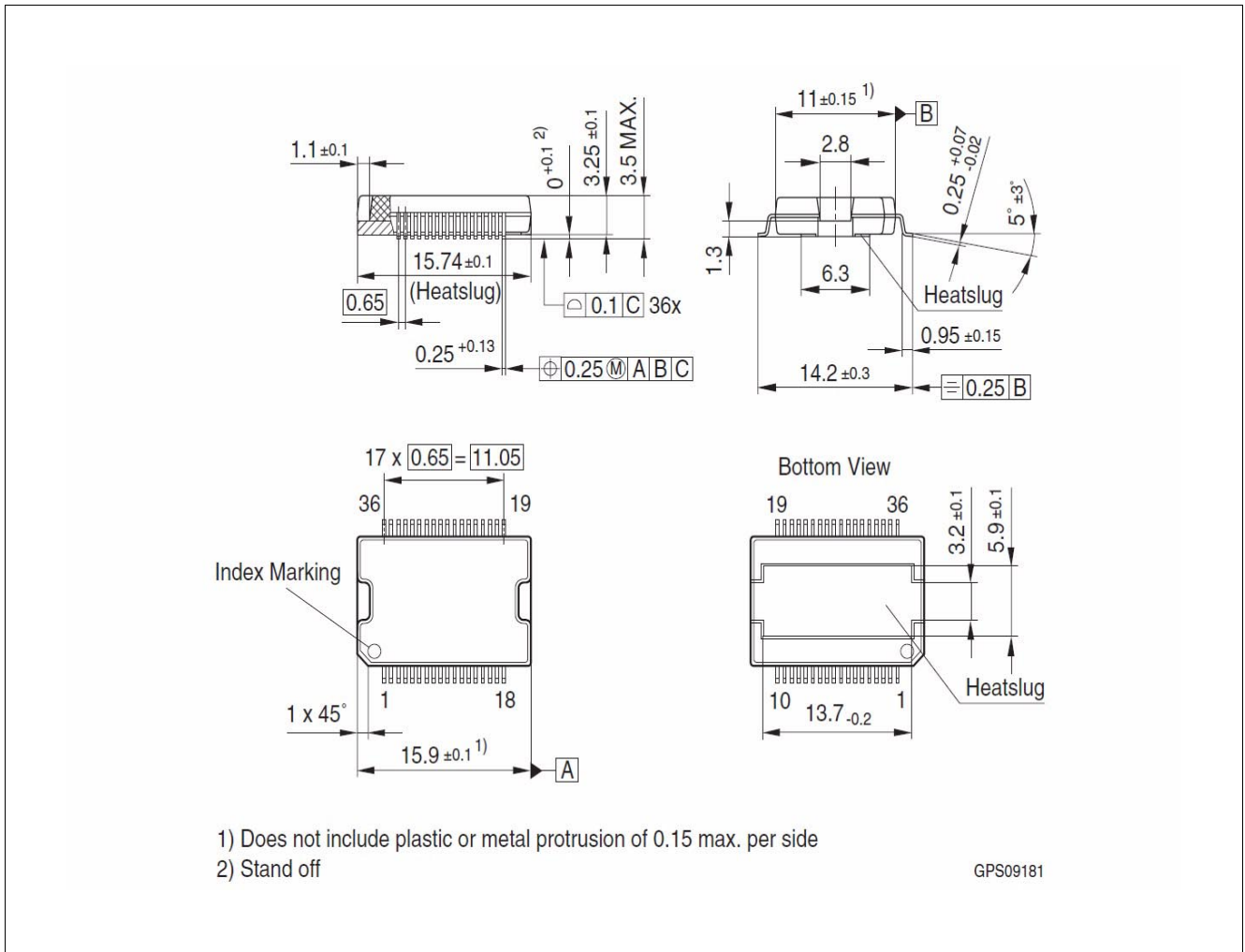


Figure 7 Protective behaviour of the ITS42008-SB-D

## 8 Package outlines and footprint



**Figure 8 PG-DSO-36 (Plastic Dual Small Outline Package, RoHS-Compliant)**

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020

## 9 Revision History

Revision	Date	Changes
v 1.01	14-05-19	Datasheet release Editorial Change on Page 11 Temperature conditions for lines 5.0.14 and 5.0.15 were corrected to 25°C and 125°C respectively
v 1.0	12-09-01	Datasheet release

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